

Amendments to the Claims

Claims 1-7 (Cancelled)

Claim 8 (Currently amended): A method of manufacturing a thin film negative temperature coefficient thermistor comprising:  
selecting a mixture of metal ~~film~~-oxides to provide the negative temperature coefficient of resistance versus temperature curve while maintaining a standardized physical size for the thermistor; and  
sputter depositing the mixture of metal ~~film~~-oxides on ~~a~~-an alumina substrate using a thin film process to form a resistive element.

61 Claim 9 (Original): The method of claim 8 further comprising:  
associating a negative temperature coefficient of resistance versus temperature curve with the thin film negative temperature coefficient thermistor.

Claim 10 (Previously presented): The method of claim 8 wherein the mixture is a mixture of manganese oxide and nickel oxide.

Claim 11 (Original): The method of manufacturing a thin film negative temperature coefficient thermistor of claim 8 further comprising:  
planarizing a substrate prior to the depositing step;  
sputtering conductor terminals;  
sputtering a passivation layer; and  
heat treating.

Claim 12 (Original): The method of claim 11 wherein the step of planarizing is applying silicon nitride film.

Claim 13 (Original): The method of claim 11 wherein the step of sputtering a passivation layer is sputtering silicon nitride film.

Claim 14 (Cancelled)

Claim 15 (Previously presented): The method of claim 8 wherein the step of depositing is sputter depositing.

Claim 16 (Currently amended): A method of manufacturing a thin film negative temperature coefficient thermistor, comprising:  
selecting a mixture of metal ~~film~~ oxides to provide desired negative temperature coefficient of resistance properties and sputter depositing the metal film oxides on ~~a~~ an alumina substrate to form a thin film resistive element.

Claim 17 (Currently amended): A method of manufacturing a thin film negative temperature coefficient thermistor of a standardized package size, comprising sputter depositing a mixture of metal ~~film~~ oxides on ~~a~~ an alumina substrate to form a thin film resistive element, the mixture of metal ~~film~~ oxides selected to provide for desired negative temperature coefficient of resistance properties while maintaining the standardized package size.

Q1 Concluded